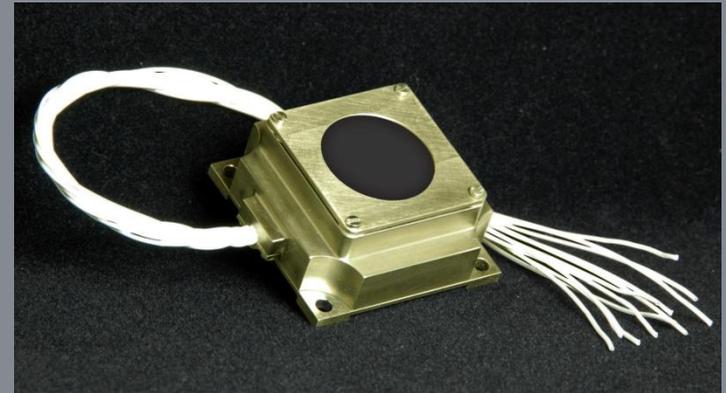
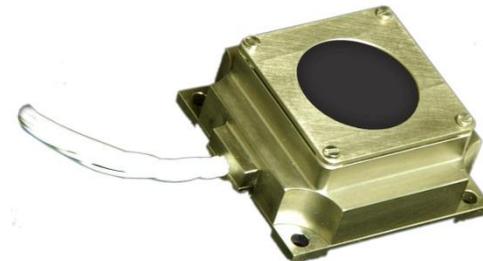
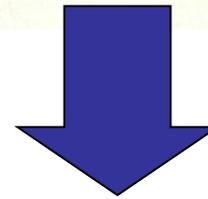
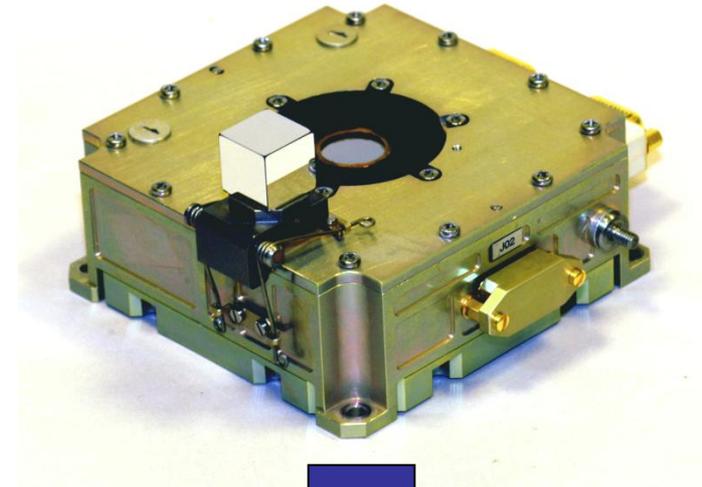


DIGITAL SUN SENSOR ON A CHIP  
PROTOTYPING  
ESTEC CONTRACT 21835/08/NL/ST  
FINAL REPORT

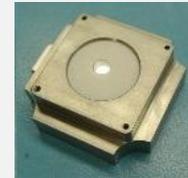
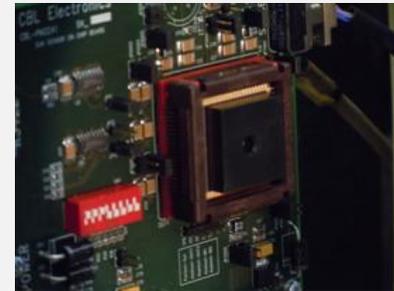
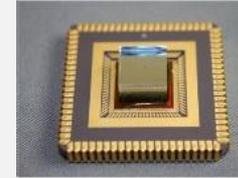
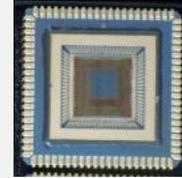


**Final Presentation**

- **Contract Overview**
- **Design**
  - Optics & MEMS
  - Sensor Chip
  - Mechanical housing mockup
- **Characterisation test results**
  - MEMS optics
  - Final package mockup
  - Sensor Chip
- **Future Development**
- **Conclusion**



- Design and manufacture a SSoC detector chip with integrated MEMS optics at prototype level
- Produce a preliminary design of the final SSoC product with justification analysis and accuracy estimation
- De-risk, by test, challenging design topics like the custom package and pixel



# SSoC: The Project Team

An **industrial team** led by **SELEX Galileo** (Italy), composed by **CMOSIS** (Belgium) and **BAE Systems** (UK) and with the support from **Thales Alenia Space** (France) expertise in AOCS, designed and developed a prototype of a miniaturized digital Sun Sensor on Chip



Long experience in attitude sensors



Machine vision sensors



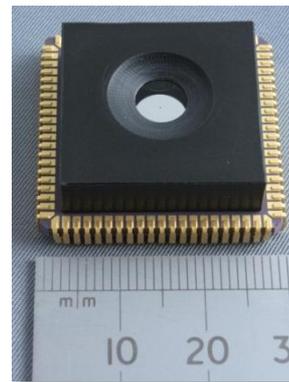
**BAE SYSTEMS**

Advanced Technology Centre

MEMS Technology



AOCS expertise



Low volume

Low mass

Low power consumption

- Implement the Digital Sun Sensor specification defined by Selex Galileo into a product that **can be qualified, industrialised** and that **fits mass, dimensions, power consumption and cost** of the final unit
- Design, manufacture, and characterize a Digital Sun Sensor chip Prototype using:
  - 0.18 micron process and true radiation hardness libraries and design
  - a System on Chip 512 x 512 pixel image sensor with 10-bitADCs, digital signal processor, SpaceWire and UART telecommand and telemetry interfaces, three linear voltage regulators for 3.3V and 1.8V, a clock oscillator, and LVDS transceivers
  - low dark current pinned diode pixel
  - 0.18 micron CMOS image sensor process (UMC) and true rad hard logic libraries
- Single chip Sun sensor design with **integrated pin-hole** and functional/performance verification
- **Custom package design** with verification of the main issues (sealing and pin hole layer bonding) by means of a **mock up**.

*The pixels developed in this contract have been designed to be re-usable in a future single-chip star tracker, with the aim to de-risk future developments*

- The contract was subdivided into two phases

- **Phase 1 - design**

- preliminary design of the final SSoC product with justification analysis and accuracy estimation
- prototype chip design up to tape-out
- electrical breadboard design

The completion of phase1 was carried out with the DDR of the chip and the CDR of the sensor unit

- **Phase 2 - manufacture and test**

- the prototype chip
- the electrical breadboard (functional representative of the final product)
- mechanical demonstration model (mock up)
- custom package mock up

The completion of phase 2 was carried out with the TRB, including test results on the chip, pin hole, sensor performance and mock ups.

# Contract Overview: programmatic history

| ID               | Description            | Location      | Contractual date | Actual Date |
|------------------|------------------------|---------------|------------------|-------------|
| <b>Phase 1</b>   |                        |               |                  |             |
| KO               | Kick Off               | Teleconf      | 15.10.2008       | 15.10.2008  |
| PM1              | Progress meeting 1     | CMOSIS        | 09.02.2009       | 23.02.2009  |
| PM2              | Progress meeting 2     | Teleconf      | 10.04.2009       | 23.04.2009  |
| DDR              | Detector Design review | CMOSIS        | 12.06.2009       | 12.10.2009  |
|                  | Close out              |               |                  | 17.02.2010  |
| CDR              | Critical design review | SELEX Galileo | 30.06.2009       | 02.12.2009  |
| <b>Phase 2</b>   |                        |               |                  |             |
| Following CCN003 |                        |               |                  |             |
| P2KO             | Phase 2 Kick off       | Teleconf      | 14.12.2009       | 02.12.2010  |
| PM3              | Progress meeting 3     | BAES          | 31.03.2010       | 15.04.2010  |
| TRR              | Test Readiness review  | Teleconf      | 3.05.2010        | 01.07.2010  |
| TRM              | Test Review meeting    | SELEC Galileo | 4.09.2010        | 16.11.2010  |

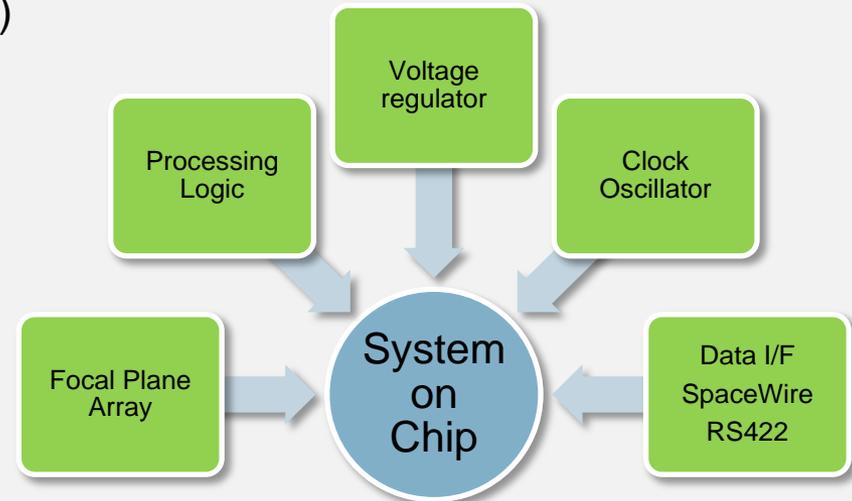
# Contract Overview: Contract Change Notice

**CCN004 is still running and results will be reported in a dedicated final report**

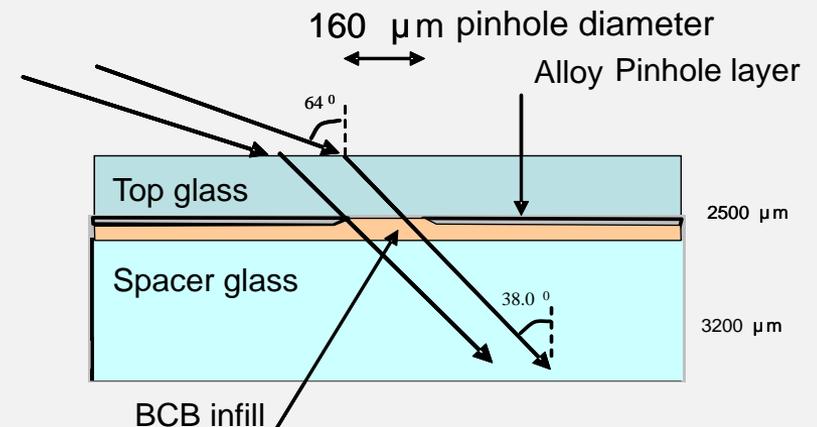
| CCN    | Title                        | Description  |
|--------|------------------------------|--|
| CCN001 | SPACEWIRE IP                 | ESA authorize SG and CMOSIS to use the Space wire IP   |
| CCN002 | METAL SHIELD                 | Feasibility study, mock-up manufacturing and verification of possible solutions for the custom package. It includes verification on different sealing methods and connections of the pin hole layer to the package case. |
| CCN003 | PHASE 2                      | ESA authorization to go on with the Phase 2 of the contract with the agreement on the phase 2 schedule. In this CCN radiation tests on pre-existing samples of 4T pixels.  |
| CCN004 | Rework and retest of Silicon | Additional activities for CMOS, repairing ADC bug and re-risking of pixels and Dc\Dc for star trackers.  |

# Design concept

- Fully digital Sun sensor (X/Y output coordinates)
- “System on chip” philosophy
- Few off chip components
- Custom design package
- Robust mechanical housing for radiation hardening



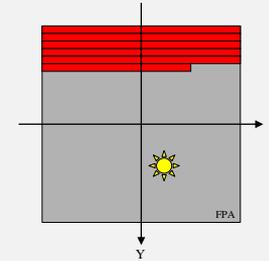
- Simple optics with pinhole
- Broad Field of View (64 deg half cone)
- Glass MEMS stack with integrated pinhole
- MEMS stack attached directly on the chip
- Aluminium alloy for pinhole layer
- Fused silica glasses bonded with BCB



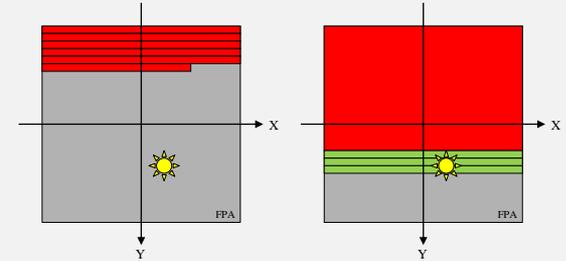
# Sun detection and tracking

- Autonomous sensor with two main operating modes
- Automatic “power on to Sun tracking” transitions
  - Sun profile programmed in chip registers
- XY Sun coordinates calculated as Sun spot barycentre
- Sun **Acquisition** Mode (SAM), default at power on
  - **Full frame** reading (programmable, nominal 511x511)
  - Automatic transition when Sun is detected
- Sun **Tracking** Mode (STM)
  - Window reading (80x80 pixels, programmable)
  - Sun tracking with **automatic window position** update
  - Nominal cycle rate 10Hz (60Hz possible)
  - Automatic **transition** to SAM when Sun is lost
- Optional 8- or 10-bit **full image download**, at reduced rate

Searching...



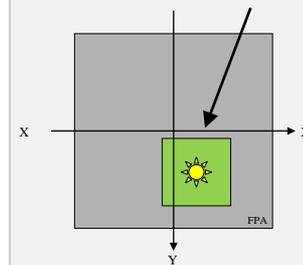
...Sun is found



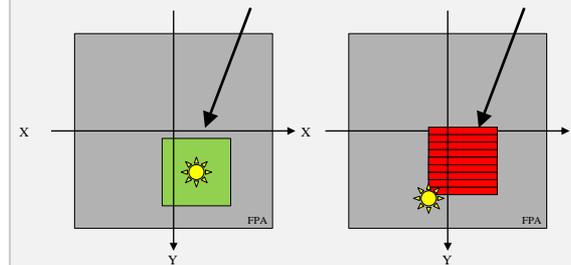
**Sun Acquisition Mode (SAM)**



Sun is present

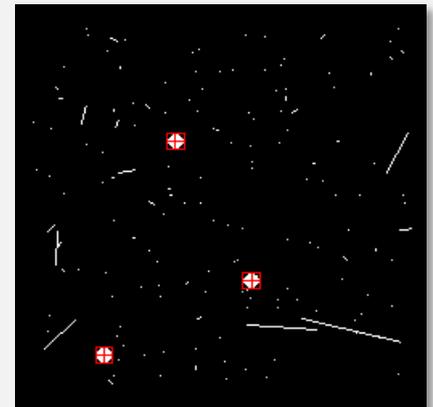


Sun is lost



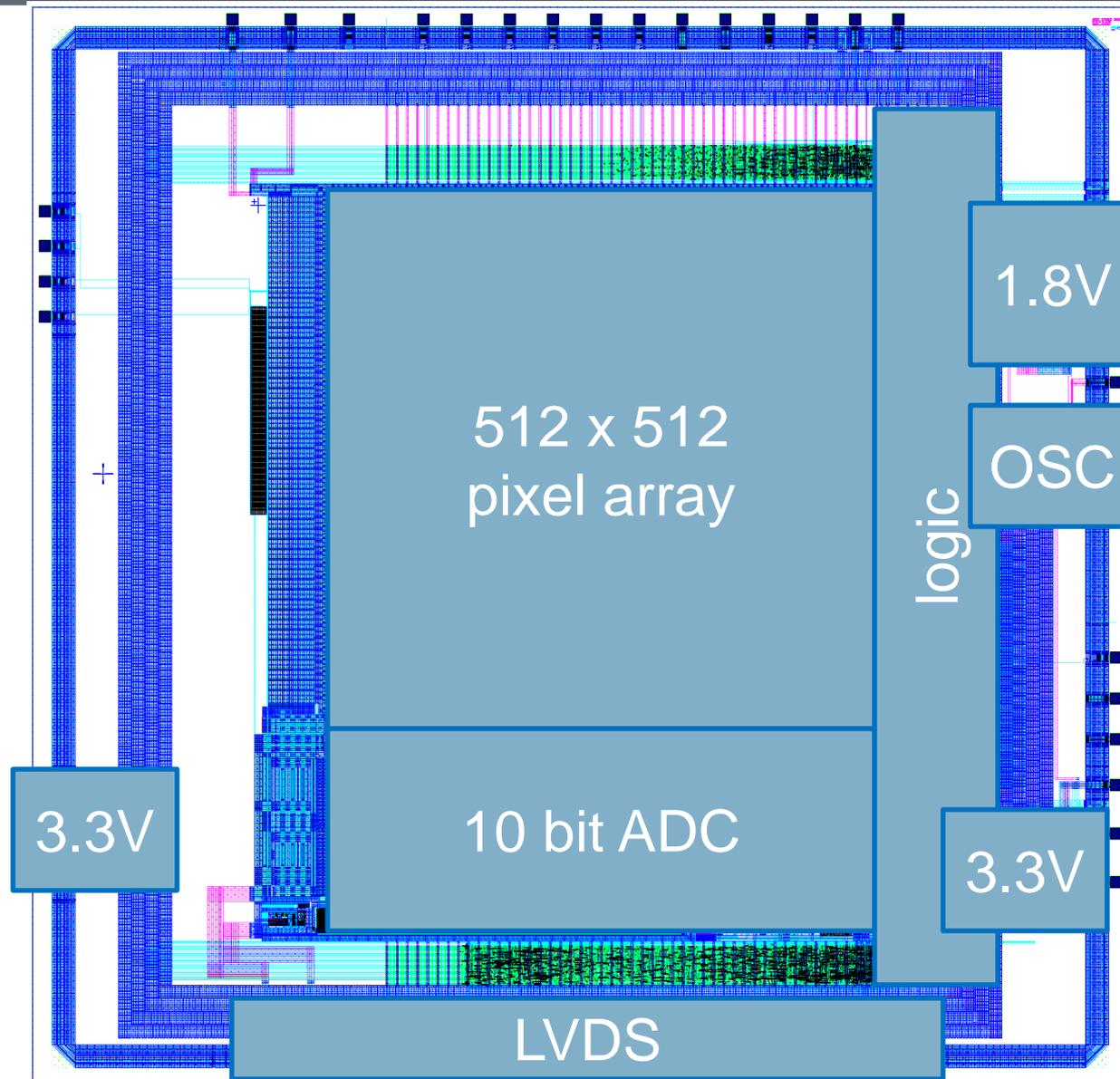
**Sun Tracking Mode (STM)**

- **Low-power** design
  - Unused analogue blocks are dynamically switched off
  - Logic clocks are dynamically gated by actual image / data contents
- Performance
  - Designed to Sun sensor performances but with Star TRacker in mind (de-risk future developments)
  - **Low-noise low-dark current** buried diode pixels
- Robustness
  - Radiation
    - All **hardened** for gamma (layout techniques, IMEC **DARE** logic cell libraries)
    - All storage elements hardened against SEUs
      - **HIT cells in DARE logic**
      - Triple Mode Redundancy in ADC
  - Power supply
    - Voltage regulators designed for input voltages  $> 5.5V$
  - Sun detection
    - Advanced image processing rejects non-sun objects
    - 2D clustering of sun image, photometric centroid



# Detector design /2

- All functions **embedded** on the same chip
- Chip connects directly to S/C **secondary supply**
- Internal voltages generated by **on chip regulators**
- On chip **oscillator** for clocks
- SpaceWire interface with **embedded LVDS drivers**
- Off chip only needs
  - 5V supply
  - Quartz crystal
  - Few resistors and capacitors



- CMOS manufacturing process selection
  - Demand for radiation robustness > 300 krad called for **radiation hard logic libraries**.
  - IMEC DARE libraries only existed in **UMC 0.18 $\mu$**  1-poly-6-metal logic process
  - Process variant: UMC 0.18 $\mu$  2-poly-4-metal Image Sensor with pinned diode pixel
  - IMEC **ported** subset of DARE rad-hard logic libraries to this process
    - ESA contract 20896/07/NL/JD
  - However ...
    - CMOSIS lacked all experience in this process.
    - This posed a **considerable risk**

- Challenges

- Pixels, electro-optical performance

- Commercial 180 nm image sensor processes are optimised for 'small' pixels (mega-pixel race).
- Sun Sensor pixel size = 10  $\mu\text{m}$ , 'large'.
- Hard to predict (and design for) dark current, full well, image lag, yield, ...
- Poor foundry support for low-volume projects.
- Normally such risks are controlled through a preparatory **experimental phase** with a pixel test chip and full process characterisation.
- This **phase was skipped** (budget, schedule!).
- **Fueled by (misplaced?) optimism.**

- Challenges (cont'd)

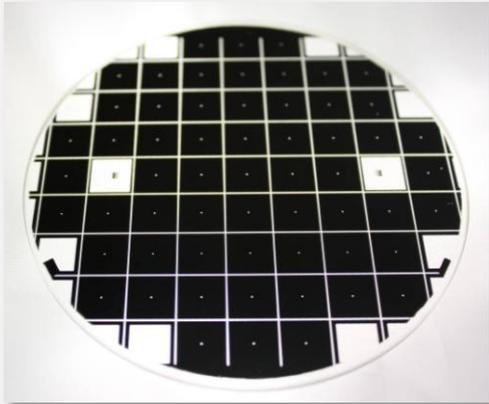
- Analogue

- All-new circuits in new process.
    - Entirely untried 10-bit column ADC architecture.
    - First-time clock oscillator.
    - First-time voltage regulators.

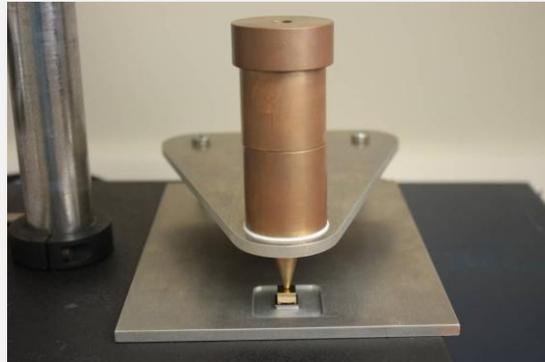
- Attempt at risk control

- Two pixel variants: normal + rad-hard by layout
  - 3 or 4 manufacturing runs planned, each with 2 or 3 process splits (implant variations)
  - This led to a lot of characterisation work
    - This is actually **still on going**, under CCN4
    - Devices with optimal Electro-Optical performance will only be demonstrated by the end of 2012
    - Devices available now are good enough for sun sensor duties

- Optical chip, glass + pinhole + glass fabricated on wafer scale
- **Chip-scale integration** for the **prototype** chip: optical chips sawn in individual pieces and bonded on already packaged sensor chips
- **Wafer-scale integration** for the **product** chip: optical chips will be aligned and bonded on the silicon wafer and then sawn and packaged



Wafer of pinhole chips, pitched to match CMOSIS wafer 44 chips/wafer



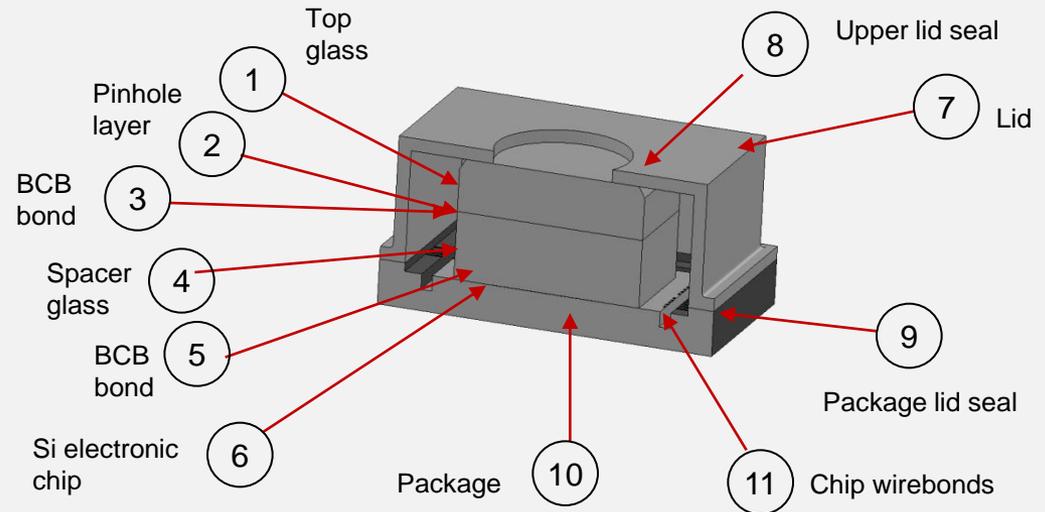
Interim Bonding jig for chip-scale bonding (bonded in vacuum chamber)



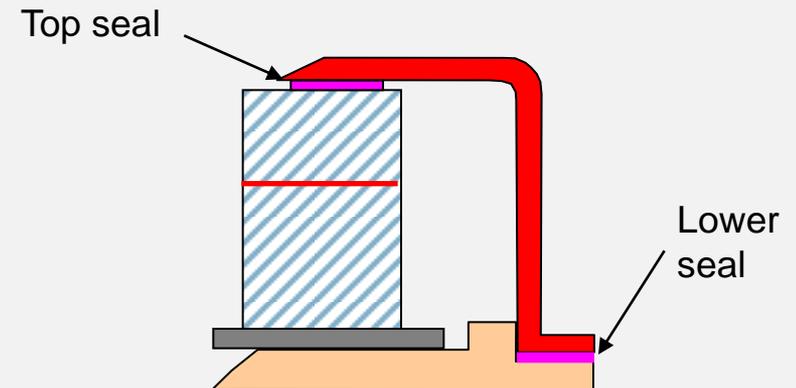
Equipment for wafer scale bonding

- Models have been constructed with:

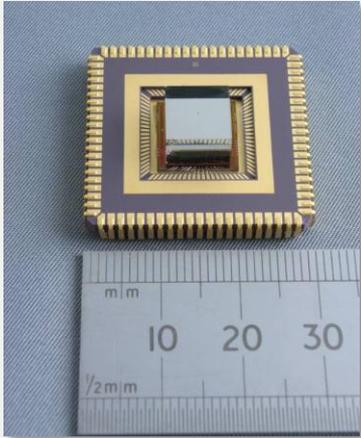
- CMOSIS APS chip
- Optical pinhole chips
- Mock-up ceramic package
- Stock lid
- Additional radiation shield



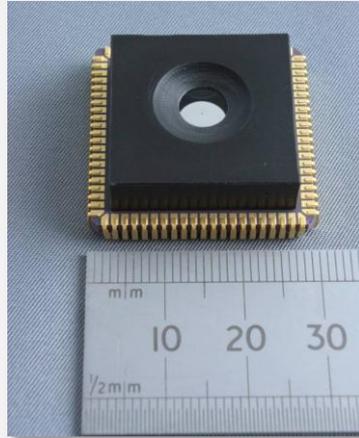
- Package **hermetically sealed** (filled with inert gas, Ar or N)
- Conventional package seal at **lower**
- Additional seal at the **top** around the optical entrance pupil



## Standard (commercial) package

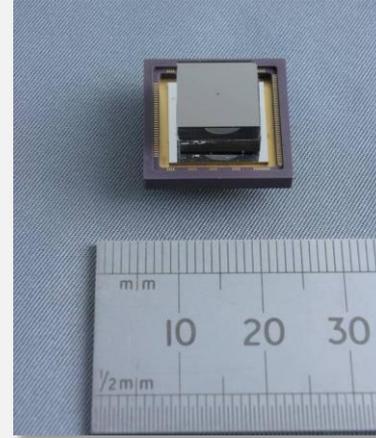


Integrated pinhole  
and packaged sensor



Chip with covering lid

## Custom package mockup



Optical chip integrated in  
representative package

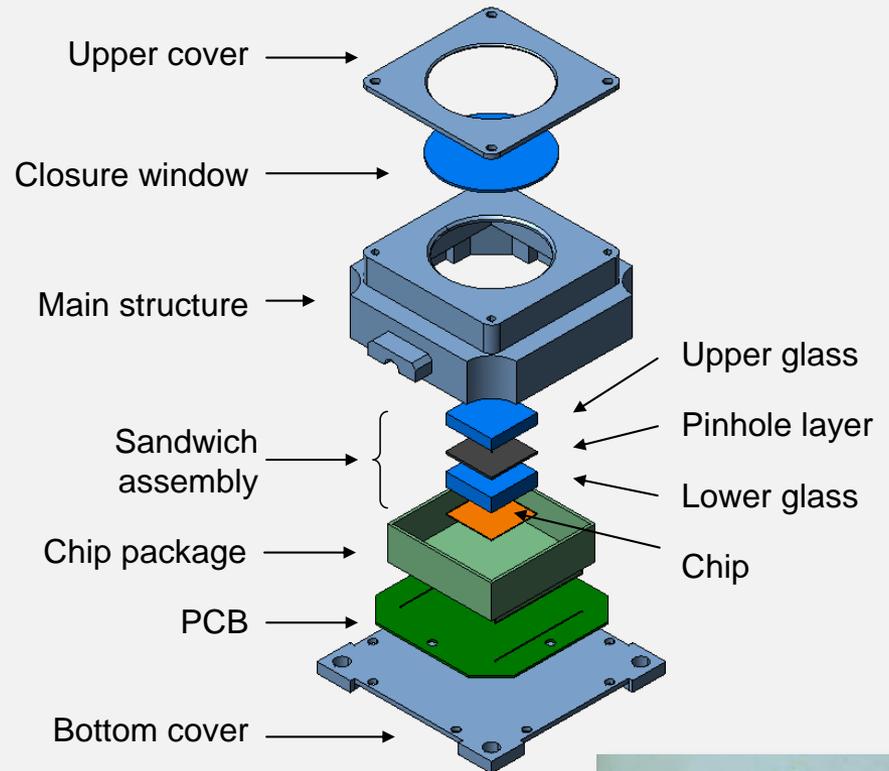


Mock-up package with  
lid for sealing tests

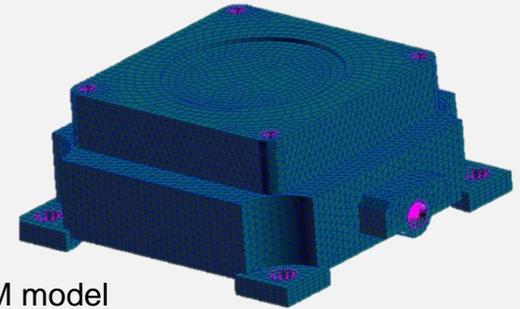
- **Standard** (larger) commercial JLCC84 package for **prototype** chips
- A **custom package** will be designed for the final **product** chips → package size shrinking
- Dedicated **metallic lid** will provide protection from **spurious light** and **radiation shield**

# Mechanical housing design

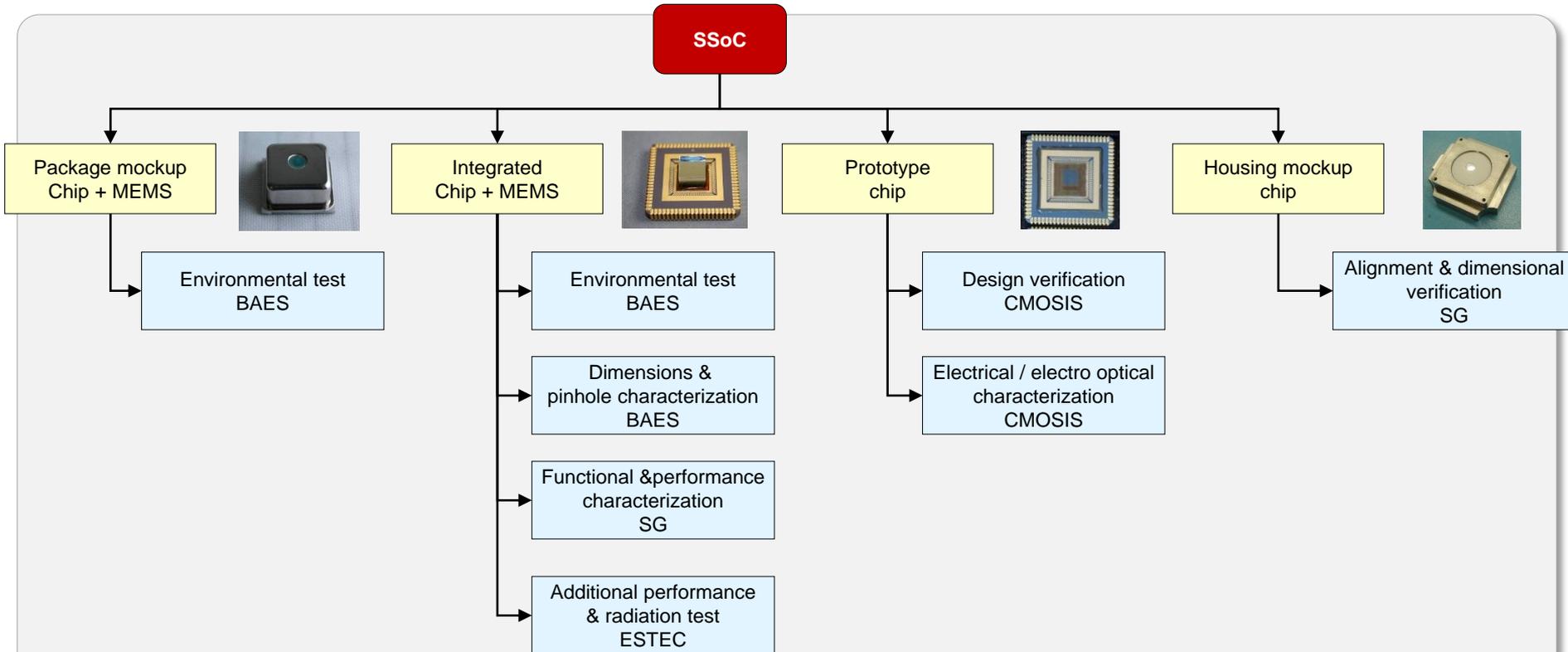
- Main structure in **Titanium** alloy to offer better radiation shielding
- **Compact** size (~40mm cube)
- Four fixation screws
- Pigtail or miniaturized connector
- Optical glass attached to the **bottom of the housing**
- Ease of chip mounting and aligning
- An **attenuation filter** can be tailored to the mission needs
- **Tiny PCB** to host the few off chip components



- A structural analysis of the SSoC preliminary mechanical design was carried out in terms of: free-free dynamic analysis, modal analysis, static stress analysis
- The structure presents a first natural frequency of 4070 Hz
- A Static stress analysis was performed with equivalent 26 grms PSD spectra resulting in positive Margins of Safety for the yield and ultimate stresses.
- The thermo elastic analysis (hot and cold cases) has shown that the displacement and rotation of the package of the chip are negligible. However, the thermo elastic behaviour of the chip/pinhole itself has to be assessed with the final mechanical design of the package
- Combination of wall thickness, use of Titanium and Kovar custom package allows adequate radiation shielding to the whole chip also at GEO for 18 years mission lifetime



- Thermal analysis was performed assuming a qualification temp. range of  $-40\text{ }^{\circ}\text{C}$  /  $+85\text{ }^{\circ}\text{C}$
- Three different thermal finishing of the housing has been considered:
  - Polished Titanium
  - VDA Kapton Tape
  - Secondary Surface Mirrors (SSM)
- In the case of isolation from the base plate the storage cold temperature must be lowered to  $-65\text{ }^{\circ}\text{C}$  to allow withstanding the hibernation case (base plate at  $-55\text{ }^{\circ}\text{C}$ , no Sun)
- VDA Kapton configuration with a conduction path to the spacecraft brings the minimum and maximum temperatures within storage limits of the chip even if with low margin



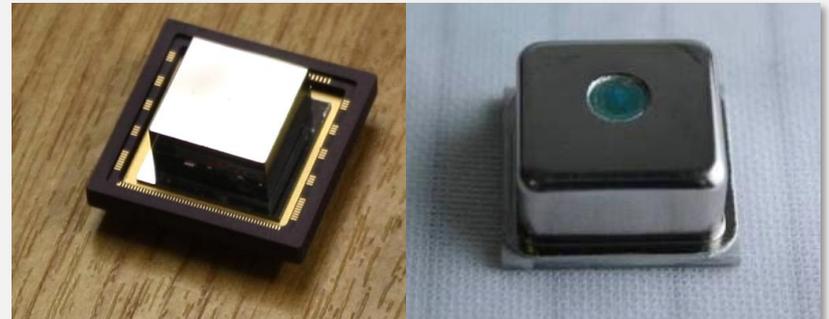
- Different items tested by SG, CMOSIS & BAES, to:
  - Prove the **design concept**
  - Validate the prototype **manufacturing process**
  - Demonstrate **chip integration** in the mechanical housing
  - Have a first estimate of the **overall accuracy**
- Additional tests performed by ESTEC to:
  - Verify **additional configuration** and operating modes
  - Characterize TID behaviour

- Custom **package mockup** and **glass MEMS stack** submitted to **environmental tests** as per common MIL-STD standards:
  - Thermal cycling (-65°C / +120°C), vibration, rapid decompression, thermal shock, fine & gross leak, RGA
- Different cover lid to package and chip **sealing variants** tested:
  - Epoxy seal
  - Silicone seal
  - Soldering seal
- Final selection of the **sealing method** will be done in the follow on contract

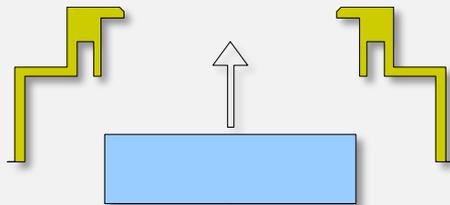


Package mockups

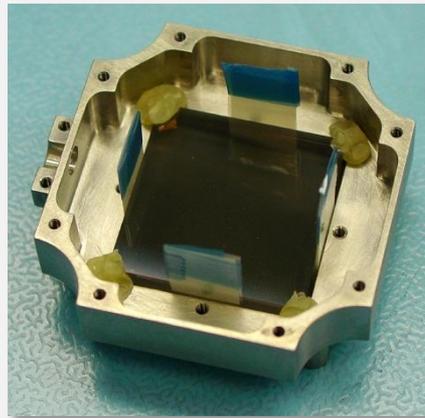
Test samples



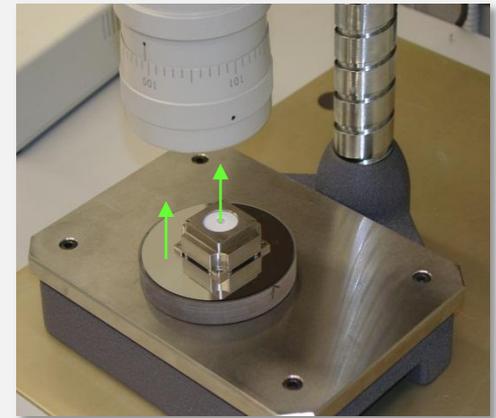
- Mass inline with **expected mass budget**
- Optical stack dummy attached to the top cover of the mechanical housing
- Easy glass dummy **mounting process**: no dedicated tool/fixtures
- Pinhole **layer is reflective**, can be used for alignment measurement
- Good parallelism (1.5') pinhole layer / mounting feet with no dedicated procedures
- Process will be maintained and optimized to reduce / **eliminate time consuming alignments**



Chip + MEMS  
attachment concept



Glass dummy inside the  
mechanical housing



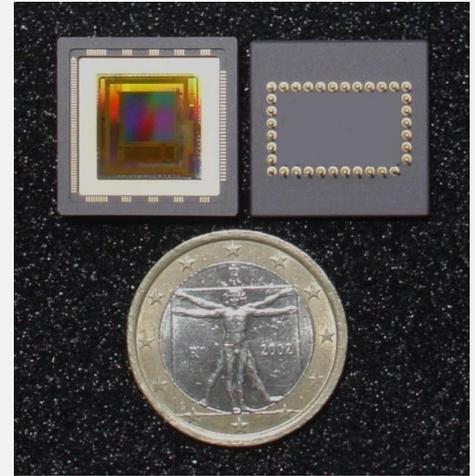
Alignment with  
autocollimator

- Sensor chip is **functional** and can reliably be demonstrated
  - Image sensor
  - ADC
  - Control and processing logic
  - Regulators, power-on-reset, oscillator
- **Issues**, non-lethal
  - Bug in ADC
    - Halves input signal range
    - Causes crosstalk: PRNU, FPN, temporal noise
    - **All unit tests were done with these additional noise sources**
  - Excessive variance of voltage regulator output
  - Temperature sensor drifts under gamma radiation
  - Aspects of Electro-Optical performance need to be improved
    - But presently good enough for sun sensor



Prototype sensor chip in standard package

- Sensor chip is **robust**
  - Selective sun image processing works
  - Tracks up to  $100^{\circ}/s$  ( $600^{\circ}/s$  in special mode)
  - No SEL or SEU in normal use
    - LET  $67 \text{ MeV}/(\text{mg}/\text{cm}^2)$ ,  $15000 \text{ part.}/(\text{s}\cdot\text{cm}^2)$
    - LET  $121 \text{ MeV}/(\text{mg}/\text{cm}^2)$ ,  $7500 \text{ part.}/(\text{s}\cdot\text{cm}^2)$
  - Supply short-term tolerant to 6.7V
  - ESD > 1800V HBM (most pins tolerate 3000V)
  - TID test by ESTEC, up to 300 kRad
  - (Proton testing deferred due to insufficient EO performance)
- Sensor chip is **small** and with low power consumption
  - Die size < 12 x 12 mm
  - Power (design goal: < 200 mW)
    - < 186 mW at 5 V with SpaceWire/LVDS (123 mW at 3.3V)
    - < 91 mW at 5V with UART/CMOS (60 mW at 3.3V)



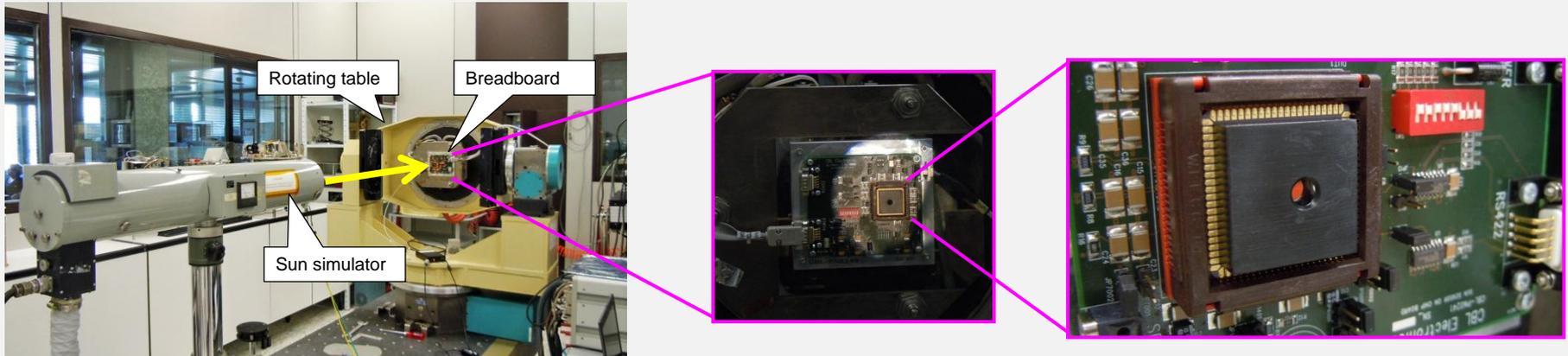
Mock-up of sensor chip in proposed custom  $\mu$ PGA package

|                  |      | target | measured |                     |
|------------------|------|--------|----------|---------------------|
| QE x FF          | %    | > 45   | 47       | averaged 400-700 nm |
| full well charge | ke-  | > 100  | 50-120   |                     |
| read noise       | e-   | < 100  | 88       |                     |
| dark current     | e-/s | < 150  | 100-6600 | RT, BOL             |
| FPN              | e-   | < 50   | 195      | (harmed by ADC bug) |

- Presently no pixel + process combination that combines:
  - low dark current
  - high full well charge
  - acceptable yield
- These are required for star tracker applications.
- CMOSIS continues pixel development in CCN4 and internally-funded development.

# Prototype Sun Sensing accuracy testing

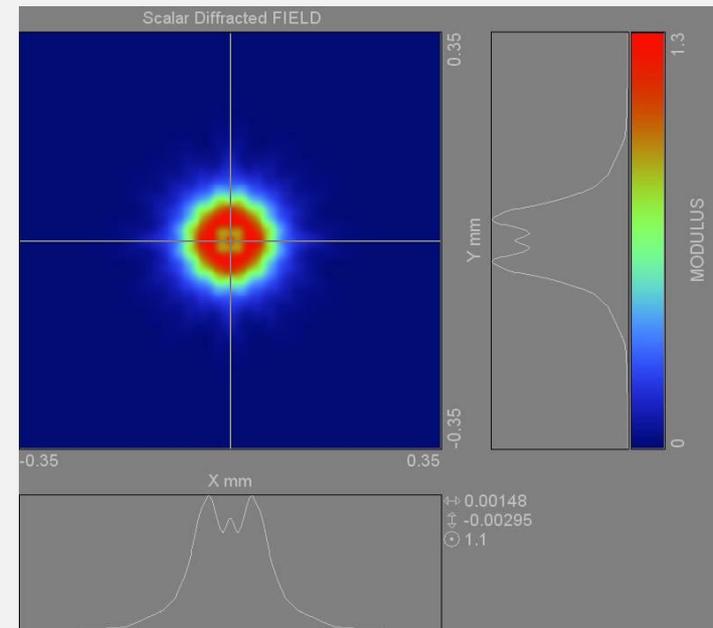
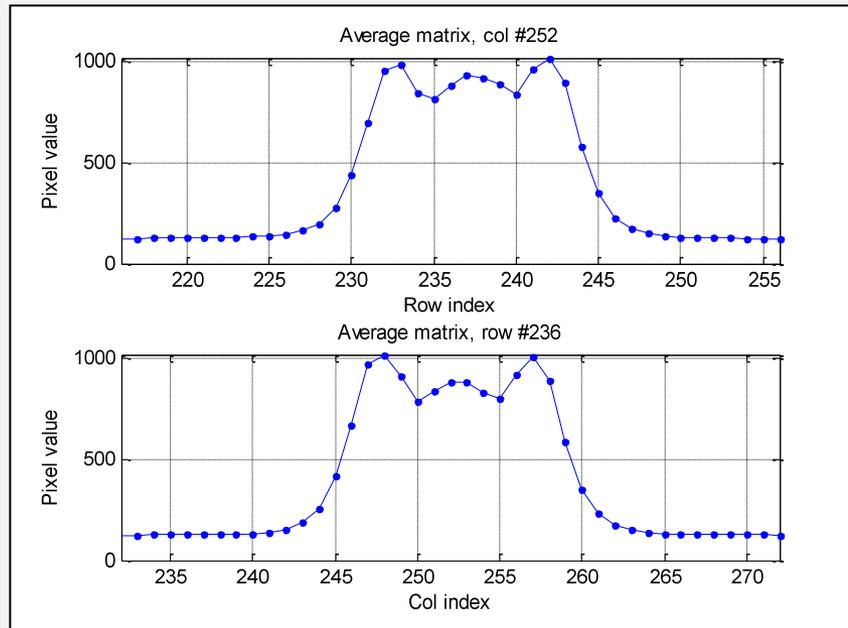
- Packaged chip + MEMS mounted on a **dedicated breadboard** for testing purposes
- Chip protected by cover lid to prevent straylight effects



- Measured **NEA** within 18 arcsec
- Prior to **any dedicated calibration** measured **bias 0.5 deg** in the whole FOV, and 0.4 deg on  $\alpha$ ,  $\beta$  axes
- A simple **focal length calibration** reduces the measured bias to 0.14 deg (whole FOV) and **0.09 deg** on  $\alpha$ ,  $\beta$  axes (5.4 arc minutes)
- Use of more complex formulas (i.e. high order polynomial) will reduce the measured bias error, to be investigated in a follow on contract

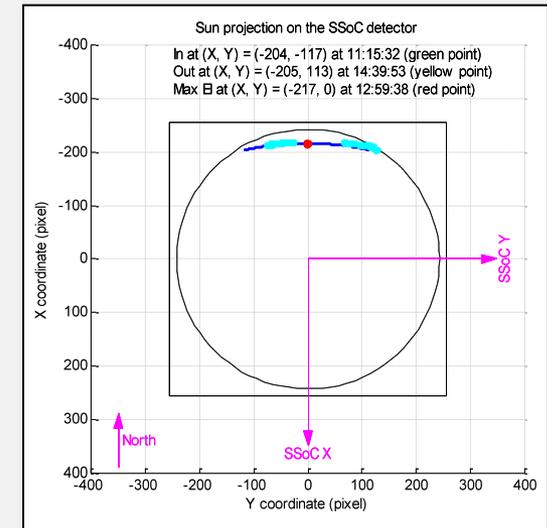
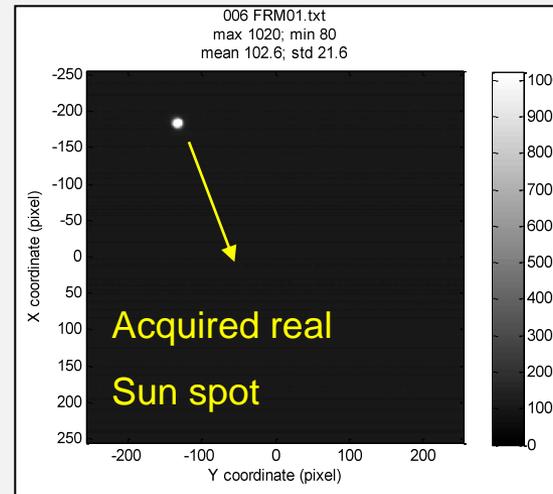
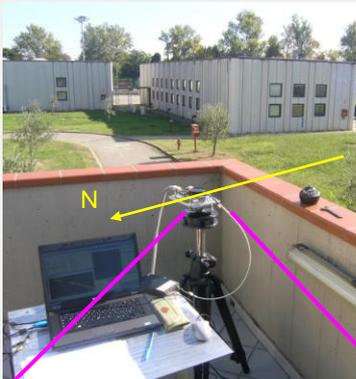
# Prototype Sun spot shape verification

- Peak / valley behaviour **confirmed by simulation** (depending on the ratio between pinhole diameter and distance from the detector)
- Simulation details:
  - Collimated in axis source at  $0.8 \mu\text{m}$  wavelength
  - $160 \mu\text{m}$  pinhole



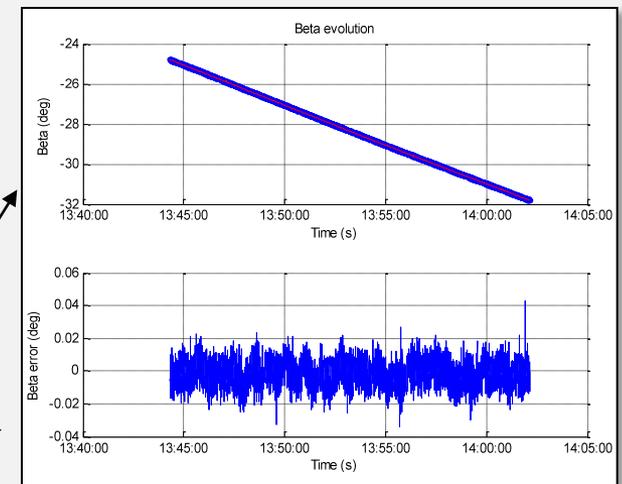
# Prototype Real Sun Test

- Sensor tested in a **real Sun** scenario for qualitative check
- Use of **attenuation filter** to avoid signal saturation
- Sun acquired and **tracked for ~100 minutes**
- Good **match** expected vs measured Sun positions
- Random error 20÷25 arcsec

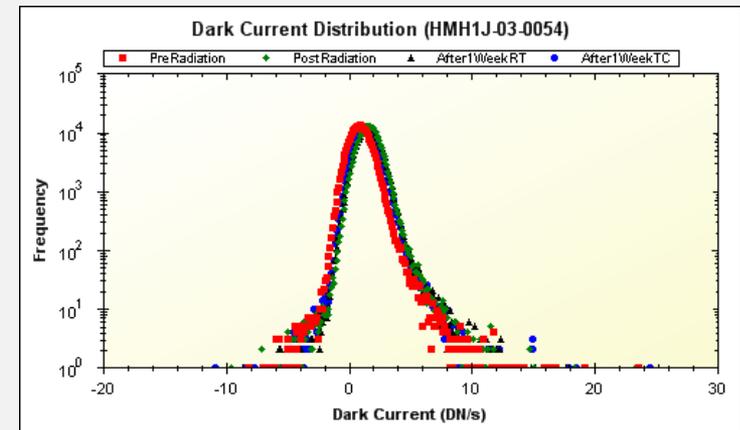


Measured  $\beta$  time evolution

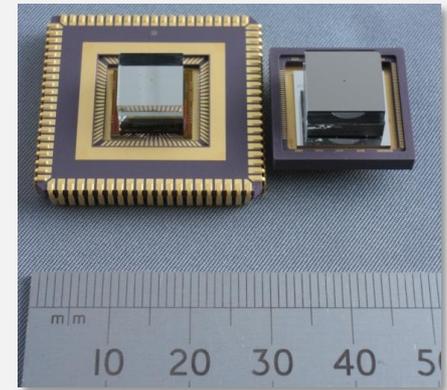
Random error



- **Cross check** of industrial results (noise, bias)
- Verify **particular configurations** and conditions not tested by the industry for schedule/cost constraints (e.g. high speed rotation)
- **TID testing**
- Test setup:
  - 1-axis rotating table
  - Dedicated breadboard
  - Sun simulator (Xenon Lamp)
- Main results:
  - NEA < 10 arcsec
  - Bias ~2 arcmin  
(6th order polynomial fit, 1 axis only rotation)
  - Sun detection & Tracking up to 220 deg/second
  - Components survived and working after 300kRad TID
  - No appreciable dark current evolution (different pixel variants and TID level)



- Contract **extension (CCN4)** for additional foundry spins
  - Full **pixel performance**, suitable also for future star tracker on chip development
  - Full characterisation, including protons
  - Repair of bug in ADC, re-spin
  - Feasibility study of DC\DC converter for future STRs
- Work planned in **future development steps** (EQM development)
  - Incorporation of all **learning** from prototype
  - **Downsizing** of the die
  - Off chip components configuration definition
  - Manufacturing of **EQM sensor chip**
  - Evaluation / qualification
  - **Wafer scale** optical chip process optimization
  - Full custom **package design**, including bonding and wire bonding methods
  - Investigation of **calibration methods** for direct  $\alpha$ ,  $\beta$  Sun angle output
  - Optimization of mounting and alignment processes at unit level to **reduce AIT cost**

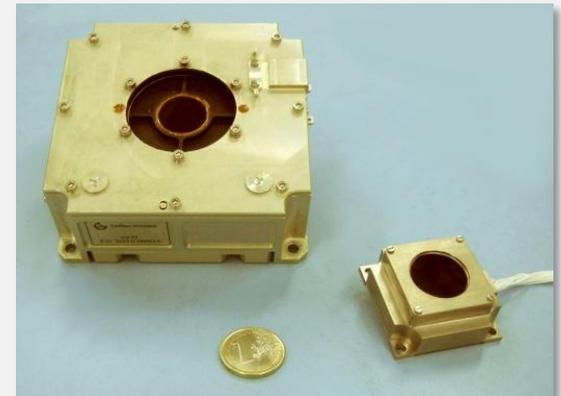


Standard vs custom package

# Summary of key results vs SSoC goals

| Physical characteristic            | Standard SG Sun Sensor (SSS)   | SSoC Prototype  | SSoC Final product goal   |
|------------------------------------|--|---|---|
| Envelope (X, Y, Z)                 | (112, 110, 43) mm  | (42, 45, 42) mm   | (40, 40, 30) mm   |
| Total mass                         | < 400gr  | 53.25gr<br>measured on the mock up without off chip electronics   | 62 gr   |
| APS Detector                       | 1024x1024 15 $\mu$ m   | 512x512 10 $\mu$ m  | 512x512 10 $\mu$ m  |
| FOV                                | 64 deg half cone   | 64 deg half cone  | 64 deg half cone  |
| Accuracy, bias error ( $1\sigma$ ) | <p>Simple calibration<br/>0.08 deg (whole FOV)<br/>0.01 deg ( 10 deg FOV)</p> <p>Iterative calibration<br/>0.02 deg (whole FOV)<br/>0.01 deg ( 30 deg FOV)</p> | <p>No calibration:<br/>0.5 deg (whole FOV)<br/>0.4 deg (<math>\alpha</math>, <math>\beta</math> axes)</p> <p>Focal length calibration:<br/>0.14 deg (whole FOV)<br/>0.09 deg (<math>\alpha</math>, <math>\beta</math> axes)</p> | <p>No calibration:<br/>0.5 deg (whole FOV)<br/>0.4 deg (<math>\alpha</math>, <math>\beta</math> axes)</p> <p>With dedicated calibration:<br/>0.02 deg (whole FOV)</p> |
| Accuracy, NEA ( $1\sigma$ )        | < 15 arcsec  | < 18 arcsec   | < 5 arcsec  |
| Resolution                         | < 0.003 deg<br>(1/64 pixel)  | < 0.002 deg<br>(1/128 pixel)  | < 0.002 deg<br>(1/128 pixel)  |
| Power Consumption                  | < 1.5 W  | 186mW chip only with on-chip regulators and clock oscillator  | < 200mW   |
| Data I/F                           | Serial Digital I/F   | SpaceWire<br>UART I/F   | SpaceWire<br>UART I/F (option)  |

- Digital **Sun Sensor on Chip** designed and developed
- **Challenging** design goals and specifications
- First **prototype chips manufactured**
- Sensor is **fully working**
- Prototype performances promising **to meet design goals**
- Coarse version with no dedicated calibration
- Accurate version with dedicated calibration
- Good **market perspectives**
- **EQM** ITT to be issued by ESA
- Full **qualification** in 2.5 years



SSoC compared with current  
SELEX Galileo Sun Sensor